

InGaAs APD-PIN Module



Model: RSAPD
InGaAs APD-PIN Module

Absolute maximum ratings

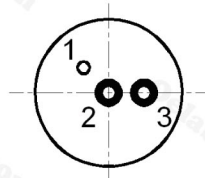
Parameter	Symbol	Value	Unit
Storage temperature	Tst	-40~+100	°C
Operating temperature	Top	-40~+85	°C
APD voltage	V _R	V _{br}	V
Soldering temperature/time	—	260/10	°C/ s

Optical & electrical characteristics(T=25°C)

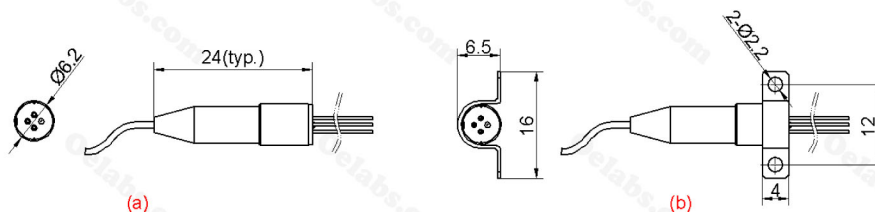
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
	Active area			55		um
R	Responsivity	λ=1310nm, M=1	0.75	0.9	-	AW
		λ=1550nm, M=1	0.9	1.05	-	
V _b	Breakdown voltage	I _d =10uA	40	50	60	V
I _d	Dark current	V _r =0.9V _b		10	50	nA
C	Capacitance	f=1MHz, V _r =0.9V _b		0.38	0.5	pF
M _{max}	Maximum multiplication factor	λ=1310nm,1550nm, I _{po} =2uA, V _r =V@I _d =1uA	25			
f _c	Cutoff frequency	M=10	2.0			GHz
	Temperature coefficient of V _b		0.09			V/°C
RL	Return loss	λ=1310nm	45			dB

PIN assignment

Pin	Function
1(case)	ground
2	APD(-)
3	APD(+)



Dimensions Diagram



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